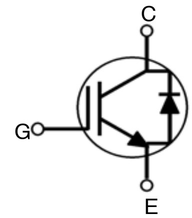
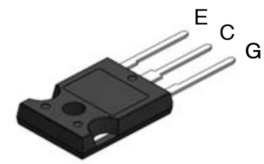
IGBT - Field Stop, Trench

650 V, 75 A

FGH75T65SQD





TO−247−3LD
CASE 340CH

Description

Using novel field stop IGBT technology, **onsemi**'s new series of field stop 4th generation IGBTs offer the optimum performance for solar inverter, UPS, Welder, Telecom, ESS and PFC applications where low conduction and switching losses are essential.

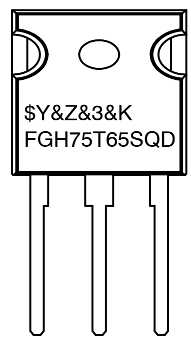
Features

- Maximum Junction Temperature : T_J =175°C
- Positive Temperature Co−efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)}$ =1.6 V(Typ.) @ I_C = 75 A
- 100% of the Parts Tested for I_{LM}(1)
- High Input Impedance
- Fast Switching
- Tighten Parameter Distribution
- These Devices are Pb−Free and are RoHS Compliant

Applications

- Solar Inverter, UPS, Welder, Telecom, ESS, PFC

MARKING DIAGRAM



$Y = **onsemi** Logo
&Z = Assembly Plant Code
&3 = Numeric Date Code
&K = Lot Code
FGH75T65SQD = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Description		Symbol	Rating	Unit
Collector to Emitter Voltage		V_{CES}	650	V
Gate to Emitter Voltage		V_{GES}	±20	V
Transient Gate to Emitter Voltage			±30	V
Collector Current	T_C = 25°C	I_C	150	A
Collector Current	T_C = 100°C		75	A
Pulsed Collector Current	T_C = 25°C	I_{LM} (Note 1)	300	A
Pulsed Collector Current		I_{CM} (Note 2)	300	A
Diode Forward Current	T_C = 25°C	I_F	75	A
Diode Forward Current	T_C = 100°C		50	A
Pulsed Diode Maximum Forward Current		I_{FM} (Note 2)	300	A
Maximum Power Dissipation	T_C = 25°C	P_D	375	W
Maximum Power Dissipation	T_C = 100°C		188	W
Operating Junction Temperature		T_J	−55 to +175	°C
Storage Temperature Range		T_{stg}	−55 to +175	°C
Maximum Lead Temp. for soldering Purposes, 1/8” from case for 5 seconds		T_L	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. V_{CC} = 400 V,V_{GE} = 15 V, I_C = 300 A, R_G = 3 Ω , Inductive Load
2. Repetive rating: Pulse width limited by max. junction temperature.

THERMAL CHARACTERISTICS

Parameter	Symbol	FGH75T65SQD−F155	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$(IGBT)	0.4	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$(Diode)	0.65	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	40	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH75T65SQD−F155	FGH75T65SQD	TO−247−3 (Pb−Free)	Tube	−	−	30

ELECTRICAL CHARACTERISTICS OF THE IGBT (T_C = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Collector to Emitter Breakdown Voltage	BV_{CES}	V_{GE} = 0 V, I_C = 1 mA	650	−	−	V
Temperature Coefficient of Breakdown Voltage	$\Delta BV_{CES}/\Delta T_J$	I_C = 1 mA, Reference to 25°C	−	0.6	−	V/°C
Collector Cut−Off Current	I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0 V	−	−	250	μA
G−E Leakage Current	I_{GES}	V_{GE} = V_{GES}, V_{CE} = 0 V	−	−	±400	nA
ON CHARACTERISTICs						
G−E Threshold Voltage	$V_{GE(th)}$	I_C = 75 mA, V_{CE} = V_{GE}	2.6	4.5	6.4	V
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 75 A, V_{GE} = 15 V	−	1.6	2.1	V
		I_C = 75 A, V_{GE} = 15 V, T_C = 175°C	−	1.92	−	V

ELECTRICAL CHARACTERISTICS OF THE IGBT (T_C = 25°C unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ies}	V_{CE} = 30 V, V_{GE} = 0 V, f = 1 MHz	–	4845	–	pF
Output Capacitance	C_{oes}		–	155	–	pF
Reverse Transfer Capacitance	C_{res}		–	14	–	pF
SWITCHING CHARACTERISTICS						
Turn−On Delay Time	$t_{d(on)}$	V_{CC} = 400 V, I_C = 18.8 A, R_G = 4.7 Ω, V_{GE} = 15 V, Inductive Load, T_C = 25°C	–	23	–	ns
Rise Time	t_r		–	10	–	ns
Turn−Off Delay Time	$t_{d(off)}$		–	120	–	ns
Fall Time	t_f		–	7	–	ns
Turn−On Switching Loss	E_{on}		–	300	–	μJ
Turn−Off Switching Loss	E_{off}		–	70	–	μJ
Total Switching Loss	E_{ts}		–	370	–	μJ
Turn−On Delay Time	$t_{d(on)}$	V_{CC} = 400 V, I_C = 37.5 A, R_G = 4.7 Ω, V_{GE} = 15 V, Inductive Load, T_C = 25°C	–	26	–	ns
Rise Time	tr		–	19	–	ns
Turn−Off Delay Time	$t_{d(off)}$		–	114	–	ns
Fall Time	t_f		–	11	–	ns
Turn−On Switching Loss	E_{on}		–	746	–	μJ
Turn−Off Switching Loss	E_{off}		–	181	–	μJ
Total Switching Loss	E_{ts}		–	927	–	μJ
Turn−On Delay Time	$t_{d(on)}$	V_{CC} = 400 V, I_C = 18.8 A, R_G = 4.7 Ω, V_{GE} = 15 V, Inductive Load, T_C = 175°C	–	22	–	ns
Rise Time	t_r		–	12	–	ns
Turn−Off Delay Time	$t_{d(off)}$		–	135	–	ns
Fall Time	t_f		–	14	–	ns
Turn−On Switching Loss	E_{on}		–	760	–	μJ
Turn−Off Switching Loss	E_{off}		–	180	–	μJ
Total Switching Loss	E_{ts}		–	940	–	μJ
Turn−On Delay Time	$t_{d(on)}$	V_{CC} = 400 V, I_C = 37.5 A, R_G = 4.7 Ω, V_{GE} = 15 V, Inductive Load, T_C = 175°C	–	24	–	ns
Rise Time	tr		–	24	–	ns
Turn−Off Delay Time	$t_{d(off)}$		–	125	–	ns
Fall Time	t_f		–	10	–	ns
Turn−On Switching Loss	E_{on}		–	1520	–	μJ
Turn−Off Switching Loss	E_{off}		–	401	–	μJ
Total Switching Loss	E_{ts}		–	1921	–	μJ
Total Gate Charge	Q_g	V_{CE} = 400 V, I_C = 75 A, V_{GE} = 15 V	–	128	–	nC
Gate to Emitter Charge	Q_{ge}		–	23	–	nC
Gate to Collector Charge	Q_{gc}		–	29	–	nC

ELECTRICAL CHARACTERISTICS OF THE DIODE (T_J = 25°C unless otherwise noted)

Parametr	Symbol	Test Conditions		Min	Typ	Max	Unit
Diode Forward Voltage	V_{FM}	I_F = 50 A	T_C = 25°C	–	2.0	2.6	V
			T_C = 175°C	–	1.64	–	
Reverse Recovery Energy	E_{rec}	I_F = 50 A, dI_F / dt = 200 A/μs	T_C = 175°C	–	61	–	μJ
Diode Reverse Recovery Time	t_{rr}		T_C = 25°C	–	43	–	ns
			T_C = 175°C	–	210	–	
Diode Reverse Recovery Charge	Q_{rr}		T_C = 25°C	–	90	–	nC
			T_C = 175°C	–	1280	–	

TYPICAL PERFORMANCE CHARACTERISTICS

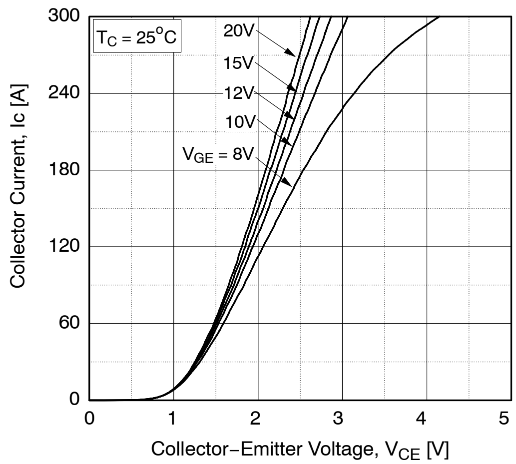


Figure 1. Typical Output Characteristics

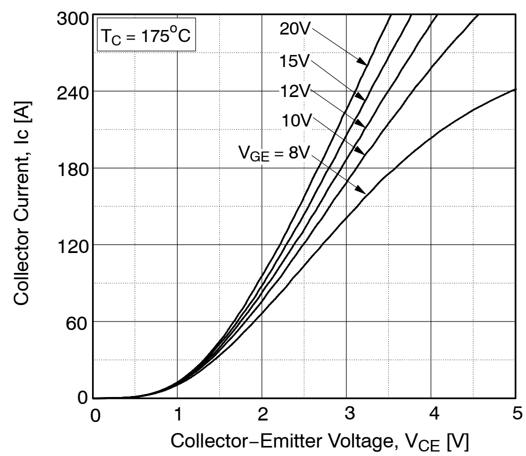


Figure 2. Typical Output Characteristics

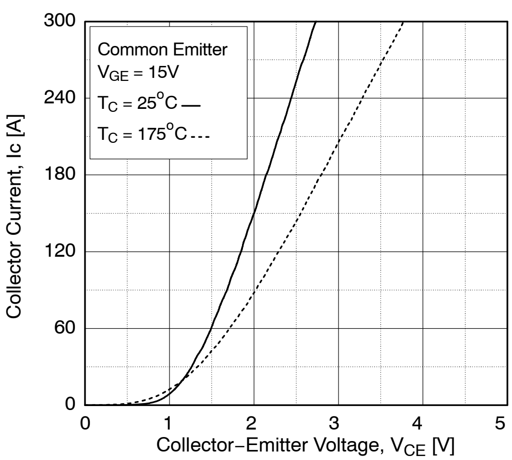


Figure 3. Typical Saturation Voltage Characteristics

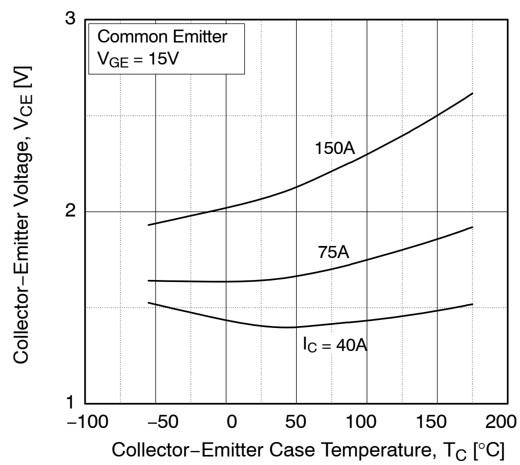


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

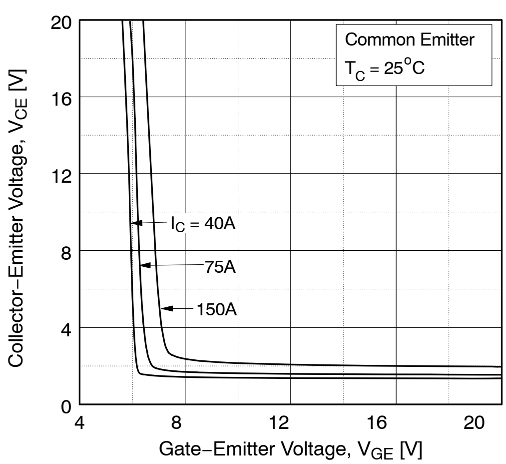


Figure 5. Saturation Voltage vs V_{GE}

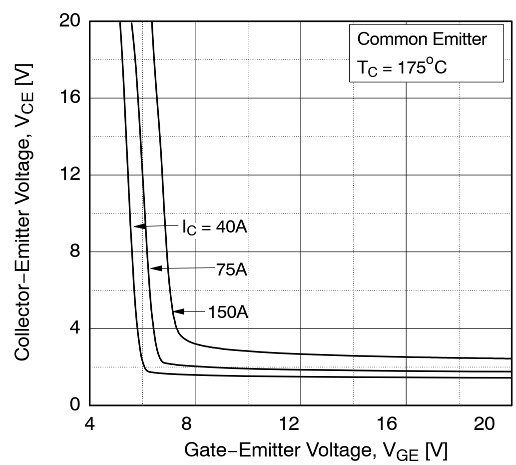


Figure 6. Saturation Voltage vs V_{GE}

TYPICAL PERFORMANCE CHARACTERISTICS

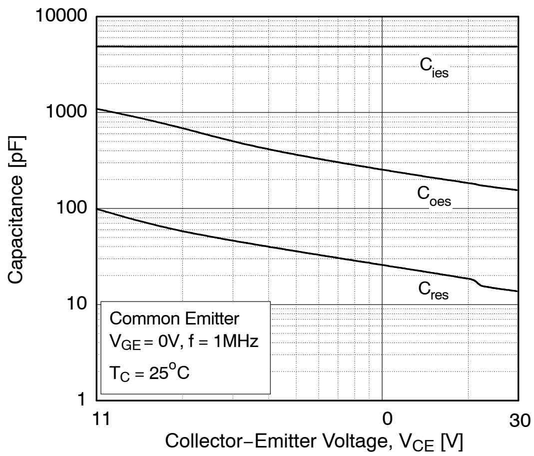


Figure 7. Capacitance Characteristics

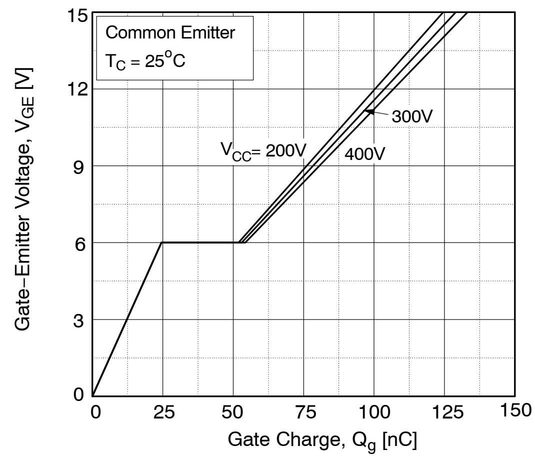


Figure 8. Gate Charge Characteristic

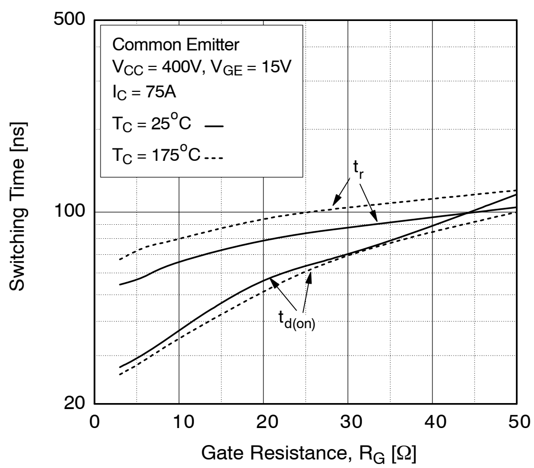


Figure 9. Turn−On Characteristics vs. Gate Resistance

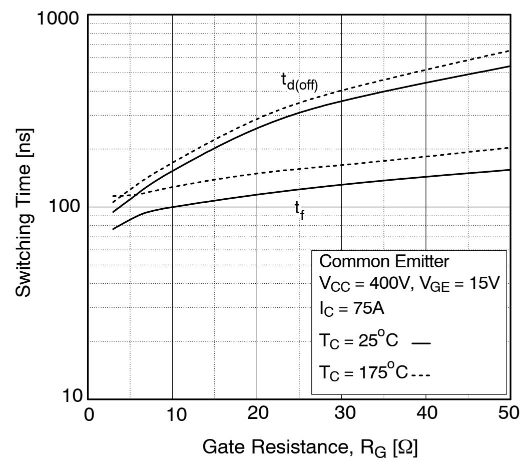


Figure 10. Turn−Off Characteristics vs. Gate Resistance

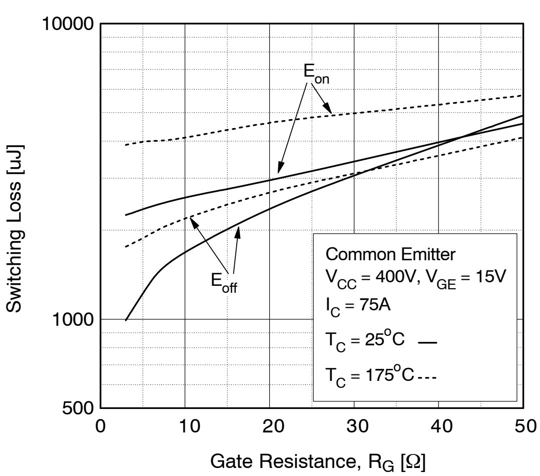


Figure 11. Switching Loss vs. Gate Resistance

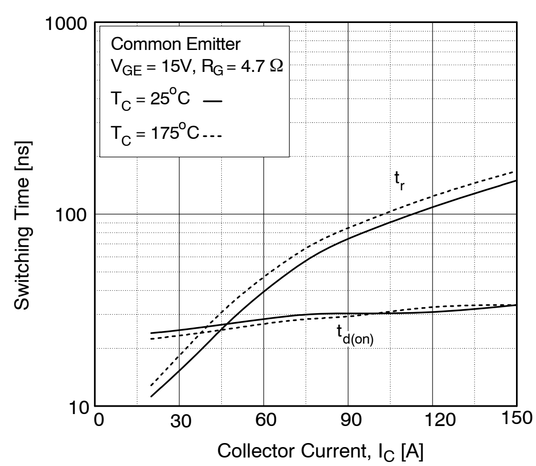


Figure 12. Turn−On Characteristics vs. Collector Current

TYPICAL PERFORMANCE CHARACTERISTICS

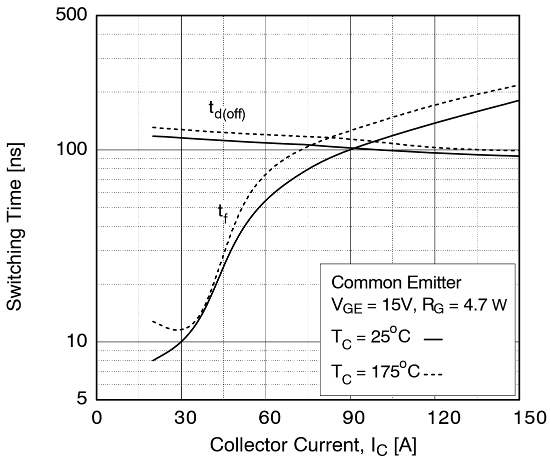


Figure 13. Turn−Off Characteristics vs. Collector Current

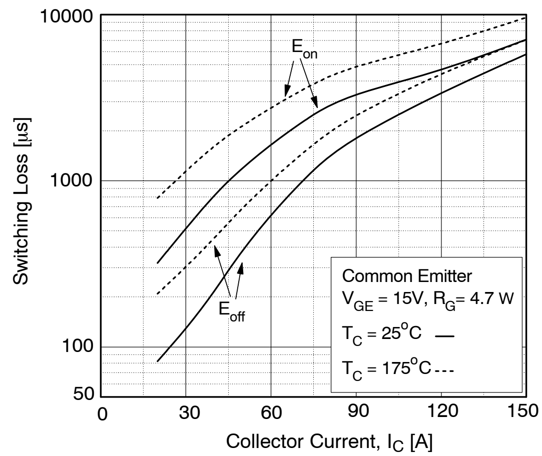


Figure 14. Switching Loss vs. Collector Current

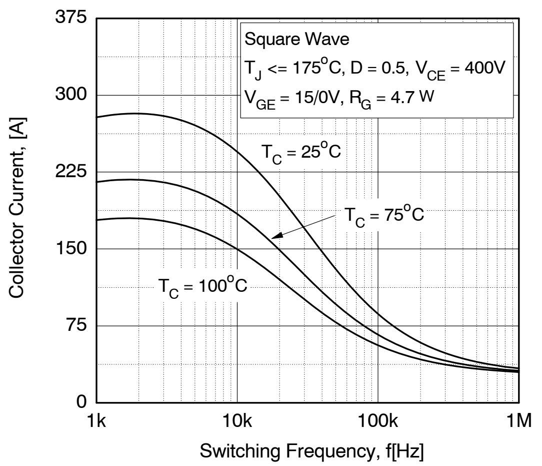


Figure 15. Load Current vs. Frequency

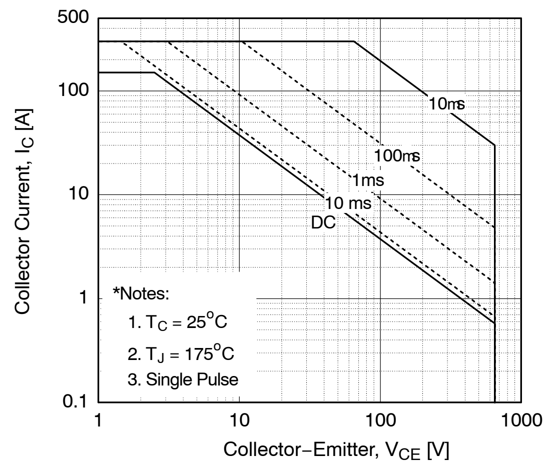


Figure 16. SOA Characteristics

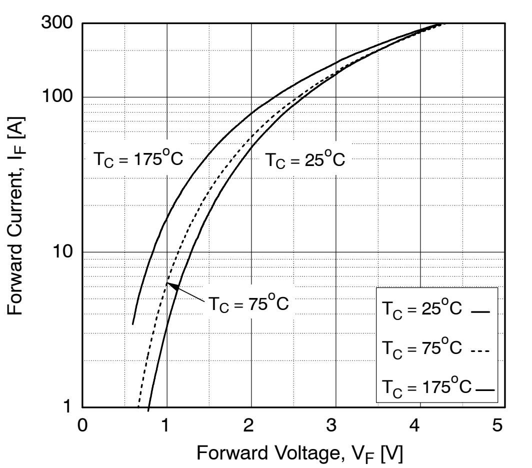


Figure 17. Forward Characteristics

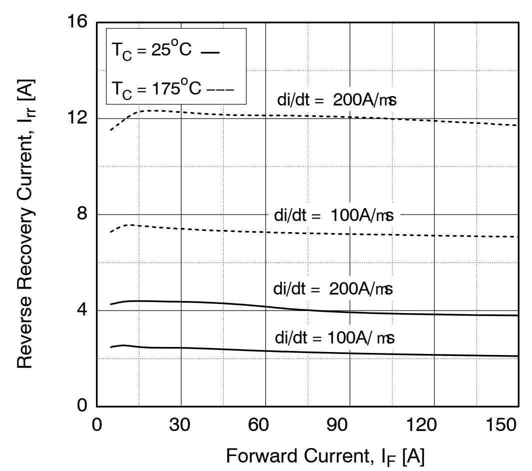


Figure 18. Reverse Recovery Current

TYPICAL PERFORMANCE CHARACTERISTICS

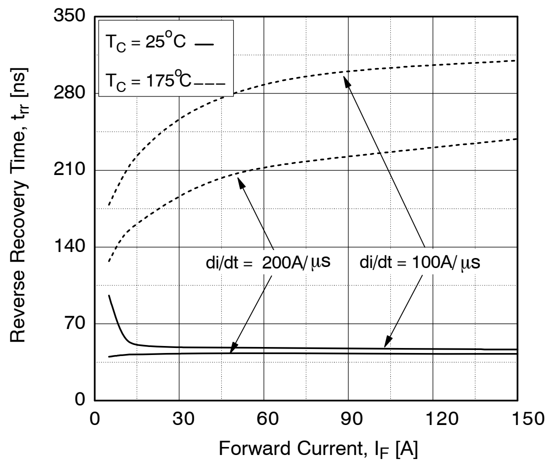


Figure 19. Reverse Recovery Time

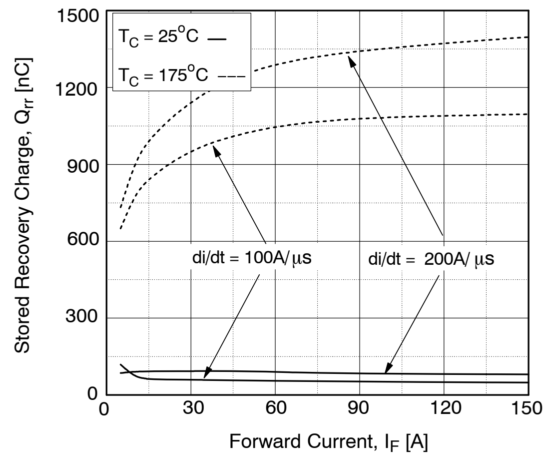


Figure 20. Stored Charge

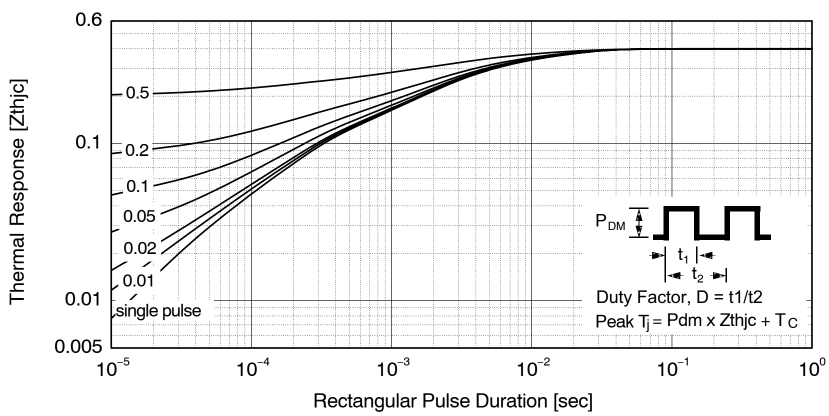


Figure 21. Transient Thermal Impedance of IGBT

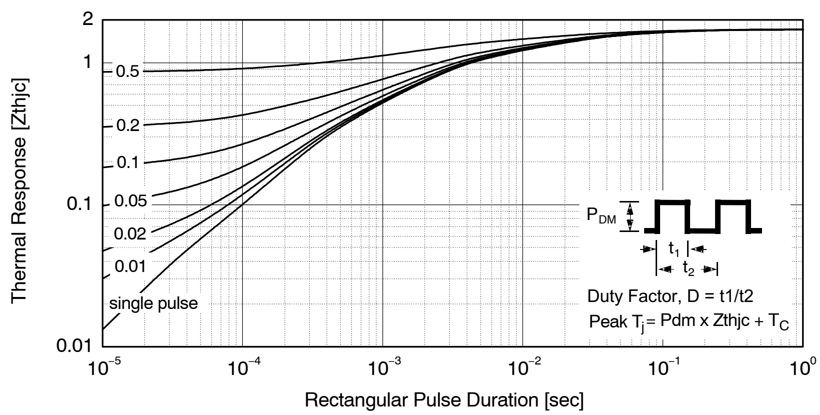


Figure 22. Transient Thermal Impedance of Diode

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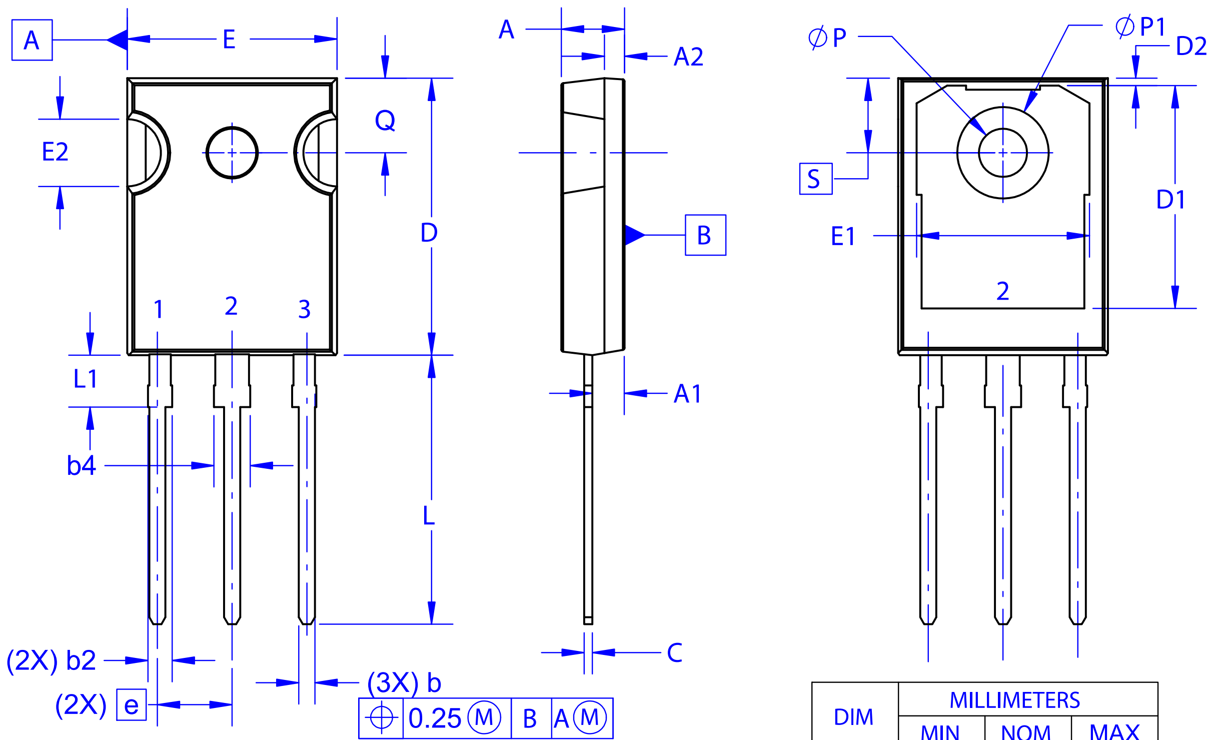
DATE 09 OCT 2019

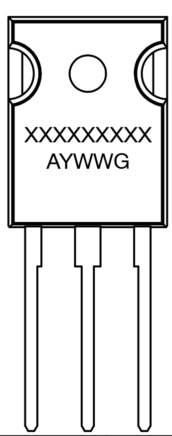


DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.29	2.475	2.66
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ØP1	6.61	6.73	6.85

NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**TO−247−3LD**	**PAGE 1 OF 1**

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